Jing-Kai Huang

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

43 5,381 25 46 g-index

46 6,105 13.3 5.36 ext. papers ext. citations avg, IF L-index

#	Paper	IF	Citations
43	Electrode Engineering in Halide Perovskite Electronics: Plenty of Room at the Interfaces <i>Advanced Materials</i> , 2022 , e2108616	24	12
42	Perovskite Quantum Dot Solar Cells Fabricated from Recycled Lead-Acid Battery Waste 2022 , 4, 120-12	7	2
41	High-Tperovskite membranes as insulators for two-dimensional transistors <i>Nature</i> , 2022 , 605, 262-267	50.4	16
40	Recent Progress in Short- to Long-Wave Infrared Photodetection Using 2D Materials and Heterostructures. <i>Advanced Optical Materials</i> , 2021 , 9, 2001708	8.1	59
39	Strain-Directed Layer-By-Layer Epitaxy Toward van der Waals Homo- and Heterostructures 2021 , 3, 442	-453	3
38	Growth of High-Quality Monolayer Transition Metal Dichalcogenide Nanocrystals by Chemical Vapor Deposition and Their Photoluminescence and Electrocatalytic Properties. <i>ACS Applied Materials & Mater</i>	9.5	3
37	Steam-Assisted Chemical Vapor Deposition of Zeolitic Imidazolate Framework 2020 , 2, 485-491		14
36	Effect of the geometry of precursor crucibles on the growth of MoS2 flakes by chemical vapor deposition. <i>New Journal of Chemistry</i> , 2020 , 44, 21076-21084	3.6	
35	Engineering Point-Defect States in Monolayer WSe. ACS Nano, 2019, 13, 1595-1602	16.7	28
34	Toward the Growth of High Mobility 2D Transition Metal Dichalcogenide Semiconductors. <i>Advanced Materials Interfaces</i> , 2019 , 6, 1900220	4.6	23
33	Gate-Tunable and Multidirection-Switchable Memristive Phenomena in a Van Der Waals Ferroelectric. <i>Advanced Materials</i> , 2019 , 31, e1901300	24	67
32	2D Materials: Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter (Adv. Mater. 18/2019). <i>Advanced Materials</i> , 2019 , 31, 1970132	24	О
31	Metal-Guided Selective Growth of 2D Materials: Demonstration of a Bottom-Up CMOS Inverter. <i>Advanced Materials</i> , 2019 , 31, e1900861	24	28
30	Growth of 2H stacked WSe2 bilayers on sapphire. <i>Nanoscale Horizons</i> , 2019 , 4, 1434-1442	10.8	11
29	One-step growth of reduced graphene oxide on arbitrary substrates. <i>Carbon</i> , 2019 , 144, 457-463	10.4	10
28	Self-Aligned and Scalable Growth of Monolayer WSe2MoS2 Lateral Heterojunctions. <i>Advanced Functional Materials</i> , 2018 , 28, 1706860	15.6	36
27	Multidirection Piezoelectricity in Mono- and Multilayered Hexagonal ⊞nSe. <i>ACS Nano</i> , 2018 , 12, 4976-49	8 36.7	133

(2013-2018)

26	Functional Two-Dimensional Coordination Polymeric Layer as a Charge Barrier in Li-S Batteries. <i>ACS Nano</i> , 2018 , 12, 836-843	16.7	63
25	Efficient electrochemical transformation of CO to C/C chemicals on benzimidazole-functionalized copper surfaces. <i>Chemical Communications</i> , 2018 , 54, 11324-11327	5.8	27
24	Evidence of indirect gap in monolayer WSe. Nature Communications, 2017, 8, 929	17.4	72
23	Metal Drganic Framework-Based Separators for Enhancing LiB Battery Stability: Mechanism of Mitigating Polysulfide Diffusion. <i>ACS Energy Letters</i> , 2017 , 2, 2362-2367	20.1	160
22	Disorder-dependent valley properties in monolayer WSe2. Physical Review B, 2017, 96,	3.3	14
21	MoirFelated in-gap states in a twisted MoS2/graphite heterojunction. <i>Npj 2D Materials and Applications</i> , 2017 , 1,	8.8	8
20	Substrate Lattice-Guided Seed Formation Controls the Orientation of 2D Transition-Metal Dichalcogenides. <i>ACS Nano</i> , 2017 , 11, 9215-9222	16.7	64
19	Multilayer Graphene-WSe Heterostructures for WSe Transistors. <i>ACS Nano</i> , 2017 , 11, 12817-12823	16.7	65
18	Scalable Patterning of MoS2 Nanoribbons by Micromolding in Capillaries. <i>ACS Applied Materials & Amp; Interfaces</i> , 2016 , 8, 20993-1001	9.5	21
17	Visualizing band offsets and edge states in bilayer-monolayer transition metal dichalcogenides lateral heterojunction. <i>Nature Communications</i> , 2016 , 6, 10349	17.4	99
16	Laterally Stitched Heterostructures of Transition Metal Dichalcogenide: Chemical Vapor Deposition Growth on Lithographically Patterned Area. <i>ACS Nano</i> , 2016 , 10, 10516-10523	16.7	41
15	Photoluminescence Enhancement and Structure Repairing of Monolayer MoSe2 by Hydrohalic Acid Treatment. <i>ACS Nano</i> , 2016 , 10, 1454-61	16.7	137
14	Graphite edge controlled registration of monolayer MoS2 crystal orientation. <i>Applied Physics Letters</i> , 2015 , 106, 181904	3.4	32
13	Ultrahigh-gain photodetectors based on atomically thin graphene-MoS2 heterostructures. <i>Scientific Reports</i> , 2014 , 4, 3826	4.9	678
12	Large-area synthesis of highly crystalline WSe(2) monolayers and device applications. <i>ACS Nano</i> , 2014 , 8, 923-30	16.7	732
11	Enhanced electrocatalytic activity of MoS(x) on TCNQ-treated electrode for hydrogen evolution reaction. <i>ACS Applied Materials & mp; Interfaces</i> , 2014 , 6, 17679-85	9.5	65
10	Monolayer MoSe2 grown by chemical vapor deposition for fast photodetection. ACS Nano, 2014, 8, 8582	211907	413
9	Synthesis and transfer of single-layer transition metal disulfides on diverse surfaces. <i>Nano Letters</i> , 2013 , 13, 1852-7	11.5	524

8	Seeing two-dimensional sheets on arbitrary substrates by fluorescence quenching microscopy. Small, 2013 , 9, 3253-8	11	5
7	Selective decoration of Au nanoparticles on monolayer MoS2 single crystals. <i>Scientific Reports</i> , 2013 , 3, 1839	4.9	342
6	High-gain phototransistors based on a CVD MoSImonolayer. <i>Advanced Materials</i> , 2013 , 25, 3456-61	24	743
5	High quantity and quality few-layers transition metal disulfide nanosheets from wet-milling exfoliation. <i>RSC Advances</i> , 2013 , 3, 13193	3.7	69
4	Chemical Vapor Deposited MoS2 Thin Layers and Their Applications. <i>ECS Transactions</i> , 2013 , 50, 61-63	1	3
3	Fluorescence Quenching: Seeing Two-Dimensional Sheets on Arbitrary Substrates by Fluorescence Quenching Microscopy (Small 19/2013). <i>Small</i> , 2013 , 9, 3252-3252	11	12
2	Wafer-scale MoS2 thin layers prepared by MoO3 sulfurization. <i>Nanoscale</i> , 2012 , 4, 6637-41	7.7	538
1	A Solution-Processed All-Perovskite Memory with Dual-Band Light Response and Tri-Mode Operation. <i>Advanced Functional Materials</i> ,2110975	15.6	5